

PSMN017-80BS

N-channel 80 V 17 mΩ standard level MOSFET in D2PAK Rev. 2 — 1 March 2012 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I_D	drain current	$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \text{see} \frac{\text{Figure 1}}{}$	-	-	50	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	103	W
T _j	junction temperature		-55	-	175	°C
Static char	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 ^{\circ}\text{C}; \text{see}$ Figure 12	-	- 15.2	29	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 10 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 13	-	13.7	17	mΩ
Dynamic c	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 40 \text{ V};$	-	6	-	nC
Q _{G(tot)}	total gate charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	26	-	nC
Avalanche	Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 50 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω ; unclamped	-	-	55	mJ



2. Pinning information

Table 2. Pinning information

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN017-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	80	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	35	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	50	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	200	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	103	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dr	ain diode				
Is	source current	T _{mb} = 25 °C	-	50	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	200	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 50 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω ; unclamped	-	55	mJ

PSMN017-80BS

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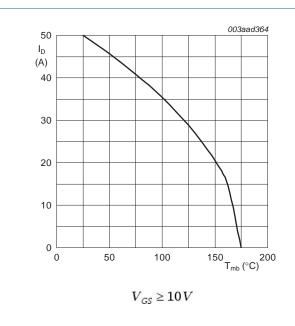


Fig 1. Continuous drain current as a function of mounting base temperature

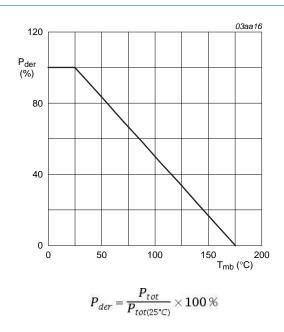
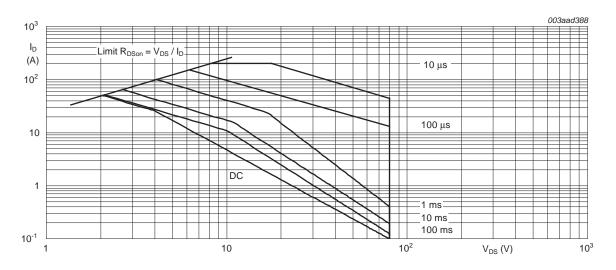


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

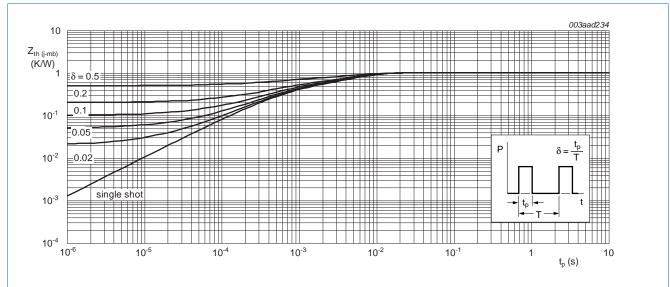


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

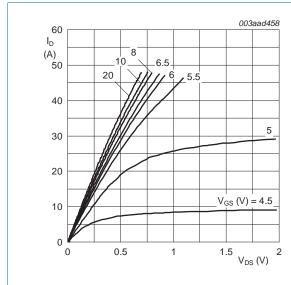
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	4.8	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	2	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μA
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
200	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 °C;$ see Figure 12	-	32.64	40.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	15.2	29	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	13.7	17	mΩ
R_{G}	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	22	-	nC
		$I_D = 25 \text{ A}; \ V_{DS} = 40 \ V; \ V_{GS} = 10 \ V;$	-	26	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	7.7	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	4.6	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	3	-	nC
Q_{GD}	gate-drain charge		-	6	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure 15}}{}$	-	4.7	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1573	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	154	-	pF
C _{rss}	reverse transfer capacitance		-	88	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 1.6 \Omega; V_{GS} = 10 \text{ V};$	-	14	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	12	-	ns
t _{d(off)}	turn-off delay time		-	27	-	ns
t _f	fall time		-	8	-	ns

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	Source-drain diode					
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.79	1.2	V
t _{rr}	reverse recovery time	$I_S = 40 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$;	-	41	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$	-	55	-	nC



 $T_j = 25 \,^{\circ}C; t_p = 300 \,\mu s$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

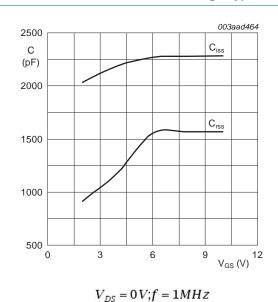
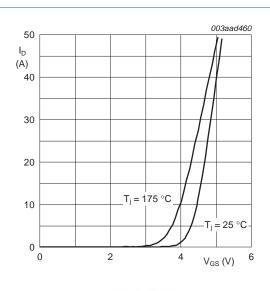
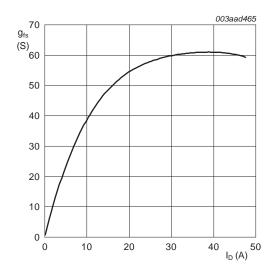


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



$$V_{DS} = 15V$$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$

Fig 8. Forward transconductance as a function of drain current; typical values

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Product data sheet

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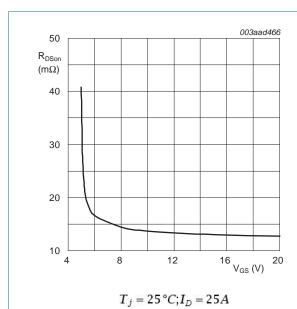
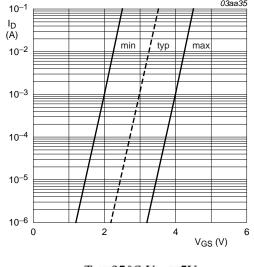


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25\,^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

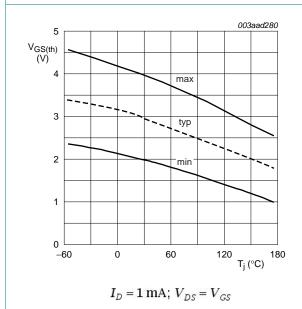


Fig 11. Gate-source threshold voltage as a function of junction temperature

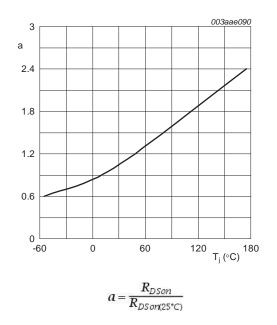
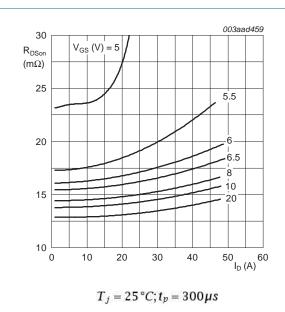


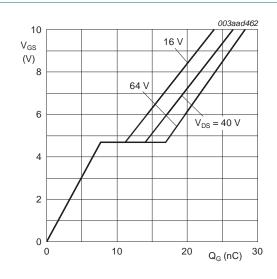
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

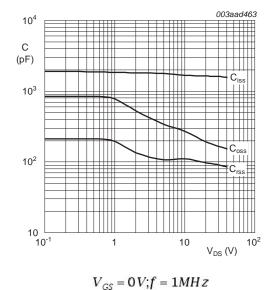


V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_{GS} Q_{GD}
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions





 $T_j = 25 \,^{\circ}C; I_D = 25A$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

Fig 15. Gate-source voltage as a function of gate charge; typical values

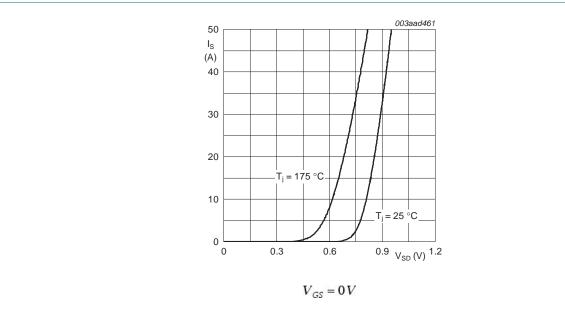


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

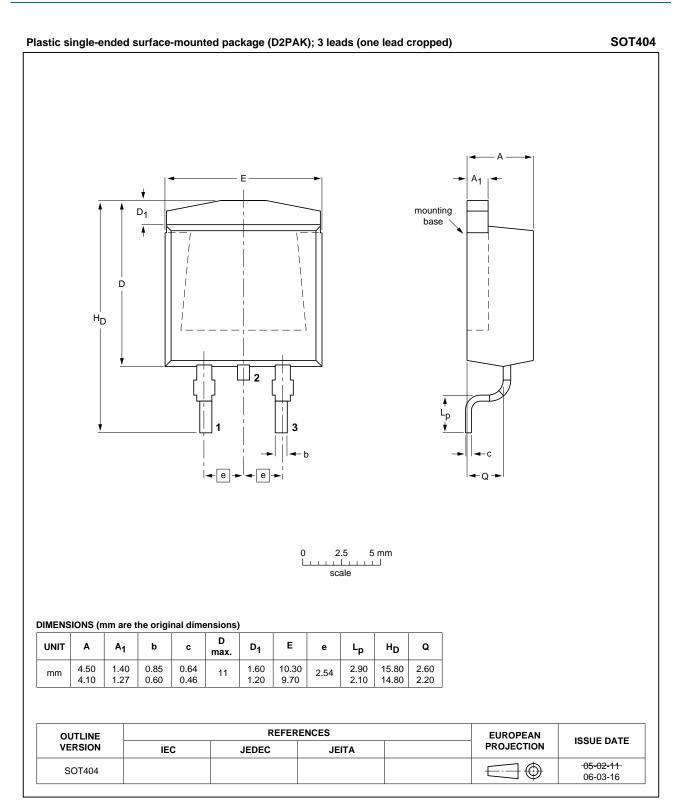


Fig 18. Package outline SOT404 (D2PAK)

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN017-80BS v.2	20120301	Product data sheet	-	PSMN017-80BS v.1
Modifications:	•	om objective to product.		
	 Various changes 	to content.		
PSMN017-80BS v.1	20111024	Objective data sheet	-	-

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9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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Nexperia PSMN017-80BS

N-channel 80 V 17 mΩ standard level MOSFET in D2PAK

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